



### CST80P03 P-Ch 30V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

#### CST80P03 Product Summary

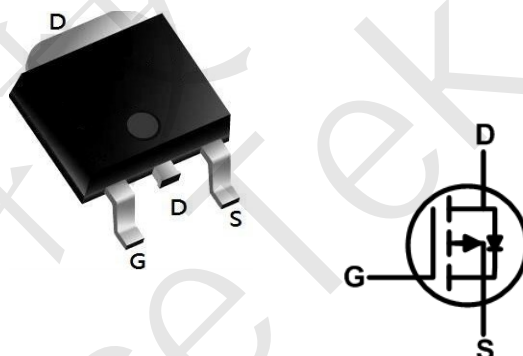
BVDSS	RDSON	ID
-30V	6.0mΩ	-80A

#### CST80P03 Description

The CST80P03 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST80P03 meet the RoHS and Gree Product requirement 100% EAS guaranteed with full function reliability approved.

#### CST80P03 TO252 Pin Configuration



#### CST80P03 Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current@-10V <sup>1</sup>	$T_C=25^\circ\text{C}$	$I_D$	-80	A
	$T_C=75^\circ\text{C}$		-42	
Pulsed Drain Current <sup>2</sup>		$I_{DM}$	-175	A
Single Pulse Avalanche Energy <sup>3</sup>		<b>EAS</b>	31	mJ
Avalanche Current		$I_{AS}$	-25	A
Total Power Dissipation <sup>4</sup>	$T_C=25^\circ\text{C}$	<b>P<sub>D</sub></b>	31.2	W
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	°C

#### Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient <sup>1</sup>	$R_{\theta JA}$	43	°C/W
Thermal Resistance from Junction-to-Case <sup>1</sup>	$R_{\theta JC}$	4	°C/W



**CST80P03 Electrical Characteristics**  $T_c = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30	-	-	V
Gate-body Leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$T_J=25^\circ\text{C}$	$V_{DS} = -24V, V_{GS} = 0V$	-	-	-1	$\mu A$
	$T_J=55^\circ\text{C}$		-	-	-5	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.5	V
Drain-Source On-Resistance <sup>2</sup>	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -12A$	-	6	8.8	m $\Omega$
		$V_{GS} = -4.5V, I_D = -8A$	-	9	14	
Forward Transconductance	$g_{fs}$	$V_{DS} = -5V, I_D = -20A$	-	28	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15V, V_{GS} = 0V, f = 1\text{MHz}$	-	4320	-	pF
Output Capacitance	$C_{oss}$		-	529	-	
Reverse Transfer Capacitance	$C_{rss}$		-	487	-	
<b>Switching Characteristics</b>						
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0\text{MHz}$	-	4.0	-	$\Omega$
Total Gate Charge	$Q_g$	$V_{GS} = -10V, V_{DS} = -15V, I_D = -15A$	-	45	-	nC
Gate-Source Charge	$Q_{gs}$		-	8.5	-	
Gate-Drain Charge	$Q_{gd}$		-	12.8	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10V, V_{DD} = -15V, R_G = 2.5\Omega, I_D = -15A$	-	18.9	-	nS
Rise Time	$t_r$		-	15.7	-	
Turn-Off Delay Time	$t_{d(off)}$		-	64.8	-	
Fall Time	$t_f$		-	36.5	-	
<b>Drain-Source Body Diode Characteristics</b>						
Diode Forward Voltage <sup>2</sup>	$V_{SD}$	$I_S = -1A, V_{GS} = 0V$	-	-	-1	V
Continuous Source Current <sup>1,5</sup>	$I_S$	$V_G = V_D = 0V$ , Force Current	-	-	-80	A

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD} = -25V, V_{GS} = -10V, L = 0.1\text{mH}, I_{AS} = -25A$
- 4.The power dissipation is limited by 150 $^\circ\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

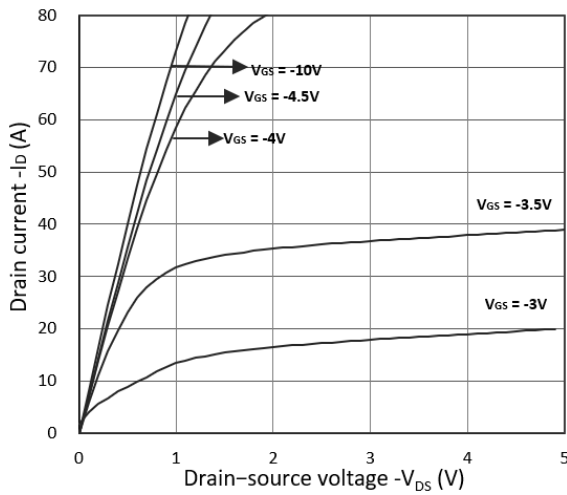


Figure 1. Output Characteristics

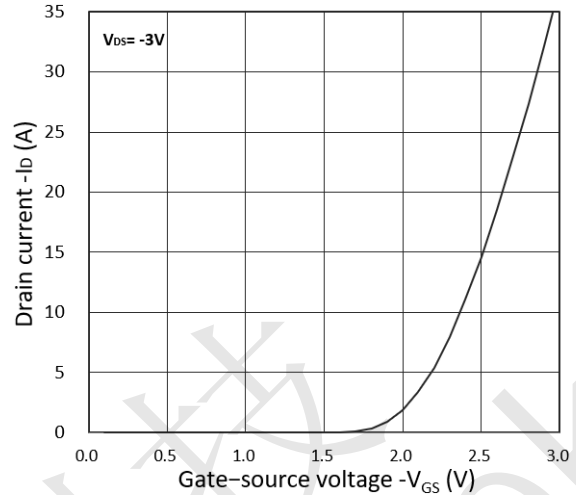


Figure 2. Transfer Characteristics

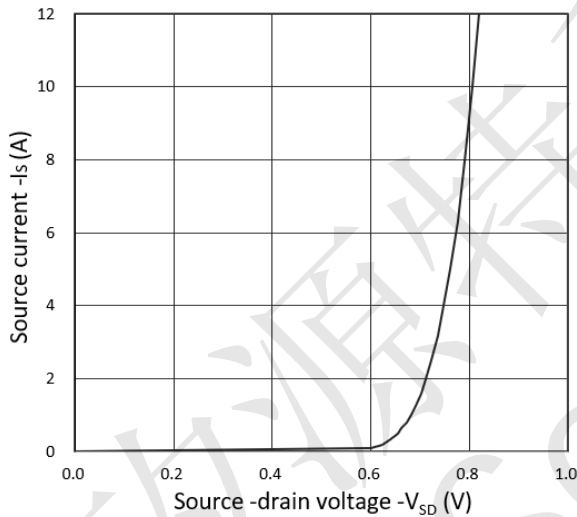


Figure 3. Forward Characteristics of Reverse

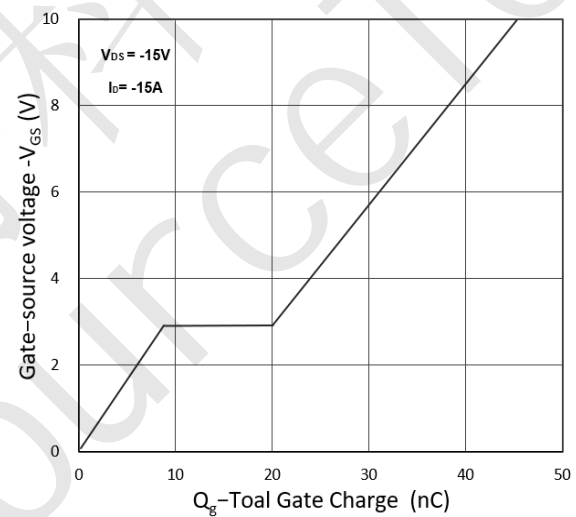


Figure 4. Gate Charge Characteristics

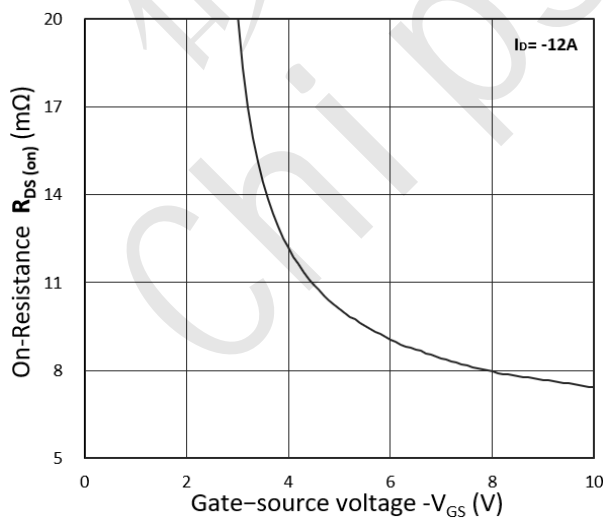


Figure 5.  $R_{DS(on)}$  vs.  $V_{GS}$

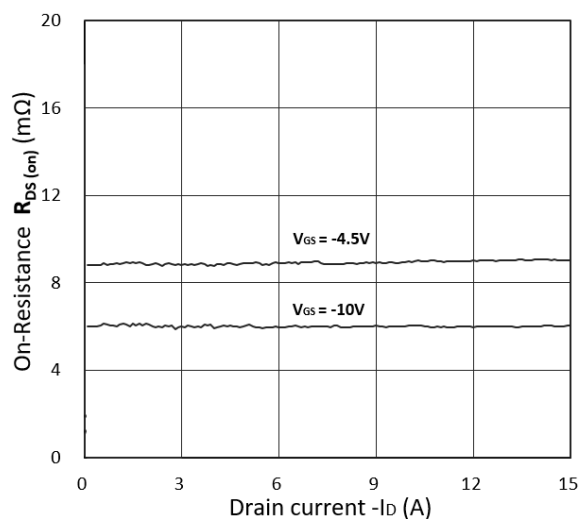


Figure 6.  $R_{DS(on)}$  vs.  $I_D$

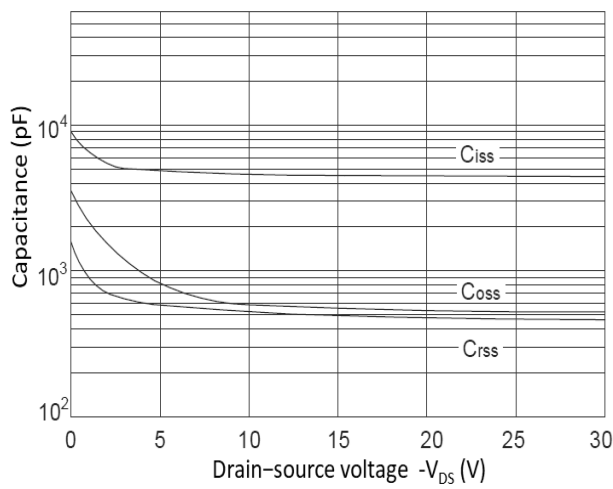


Figure 7. Capacitance Characteristics

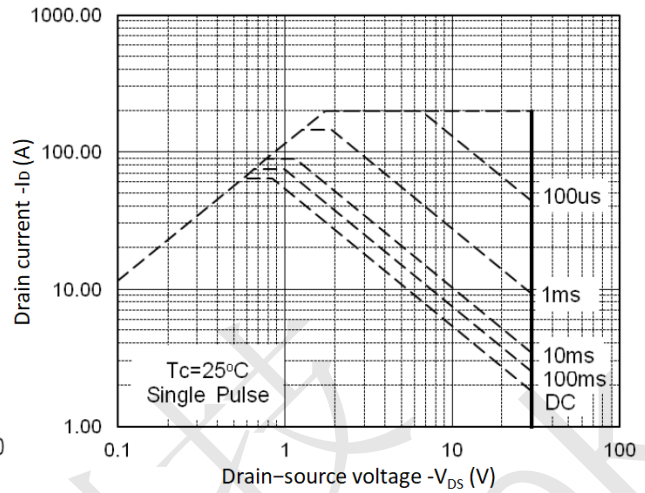


Figure 8. Safe Operating Area

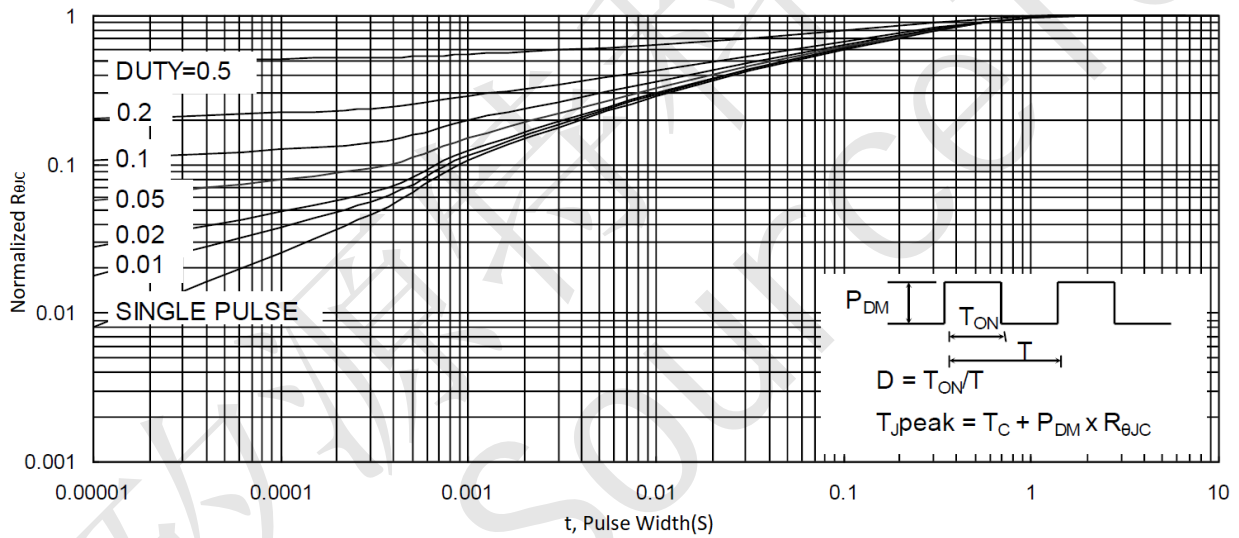


Figure 9. Normalized Maximum Transient Thermal Impedance

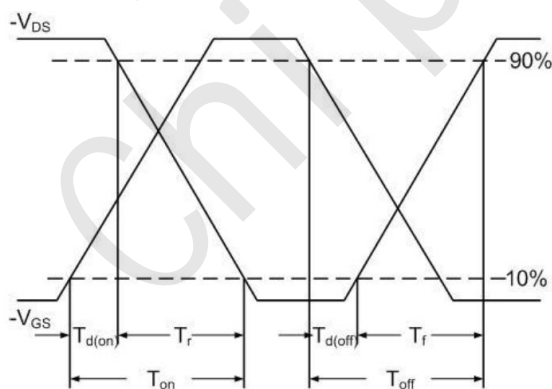


Figure 10. Switching Time Waveform

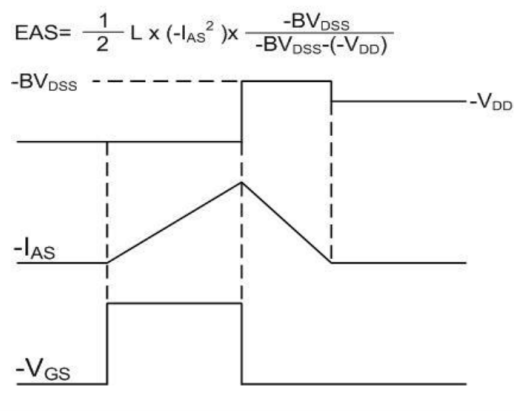
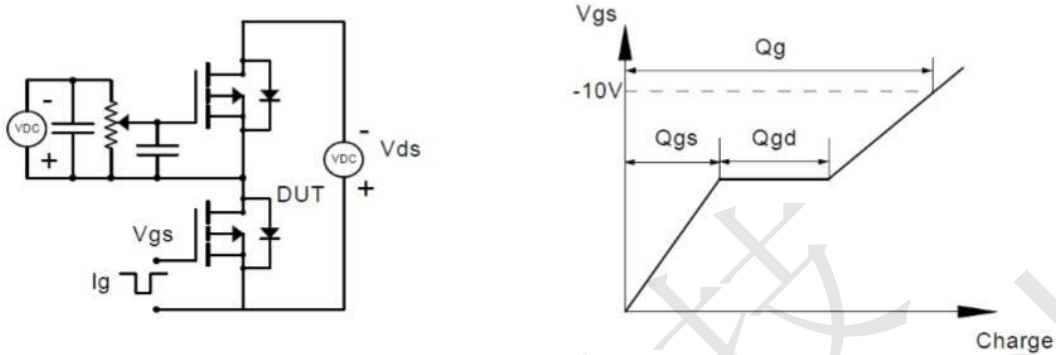


Figure 11. Unclamped Inductive Switching Waveform

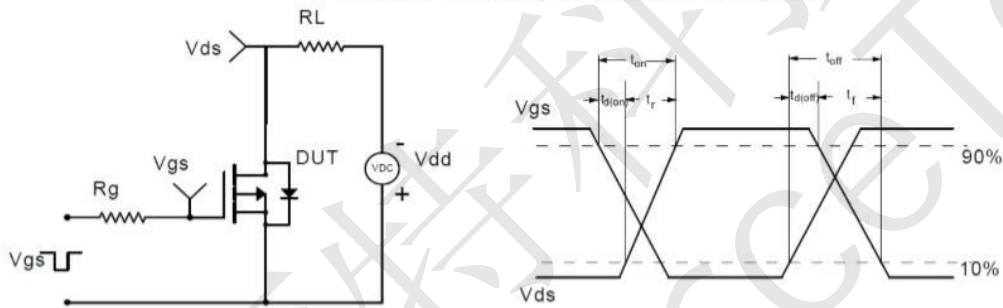


### CST80P03 Test Circuit

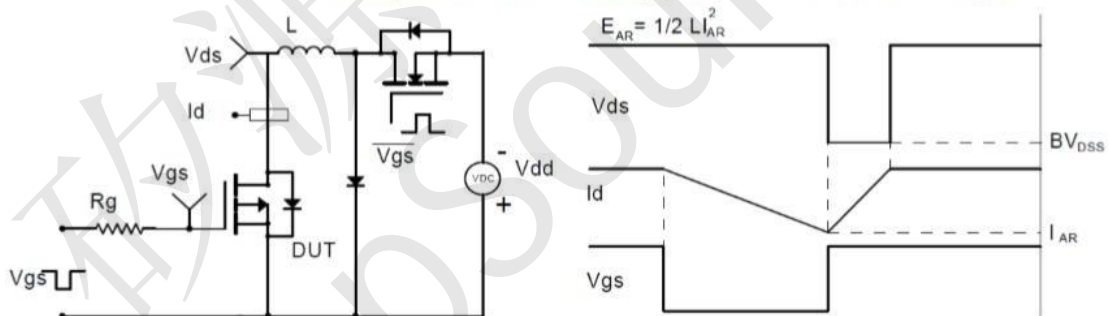
Gate Charge Test Circuit & Waveform



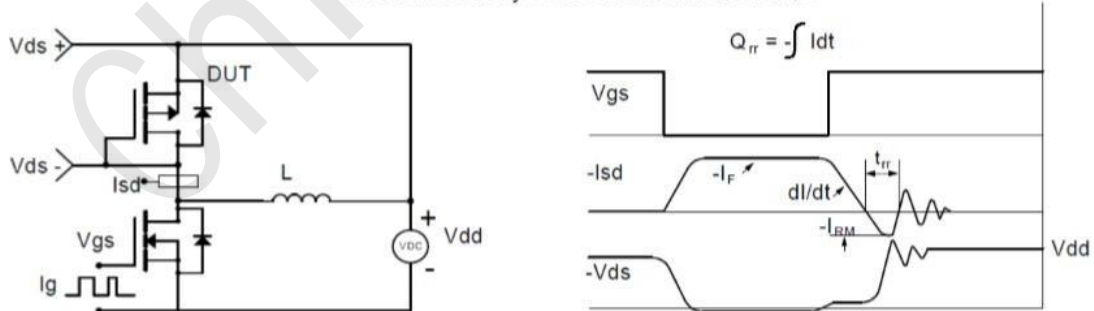
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



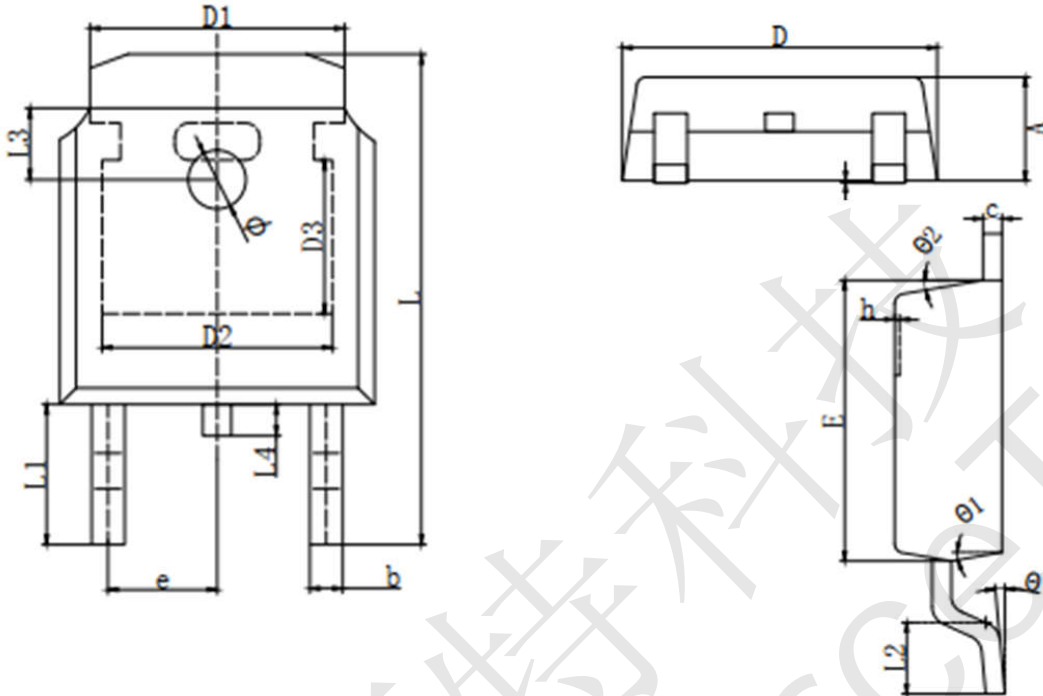
Diode Recovery Test Circuit & Waveforms







CST80P03 TO-252 Package outline



SYMBOL	MILLIMETER		SYMBOL	MILLIMETER	
	MIN	MAX		MIN	MAX
A	2.200	2.400	h	0.000	0.200
A1	0.000	0.127	L	9.900	10.30
b	0.640	0.740	L1	2.888 REF	
c	0.460	0.580	L2	1.400	1.700
D	6.500	6.700	L3	1.600 REF	
D1	5.334 REF		L4	0.600	1.000
D2	4.826 REF		$\phi$	1.100	1.300
D3	3.166 REF		$\theta$	0°	8°
E	6.000	6.200	$\theta 1$	9° TYP2	
e	2.286 TYP		$\theta 2$	9° TYP	